

Performance

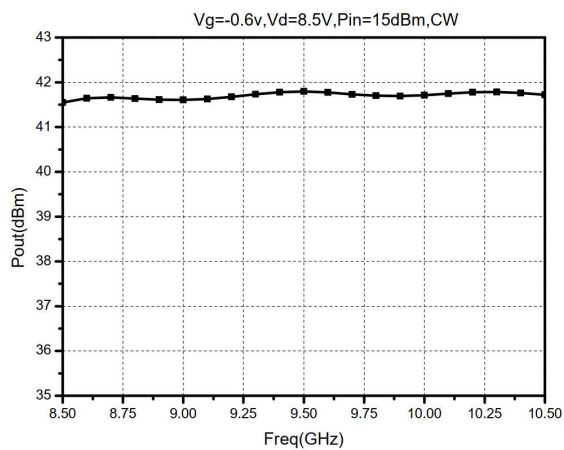
- Frequency: 8.5~10.5GHz
- Psat: 41dBm
- PAE: 40%
- Power Gain: 23dB
- Linear Gain: 27dB
- VSWRin: 1.8
- Bias Condition: 8.5V, -0.6V
- Size: 3.2*4.0mm*0.08mm
- Process: 0.35um PHEMT Technology

Electrical Specifications (Vd=8.5V, Vg=-0.6V, Freq=8.5~10.5GHz)

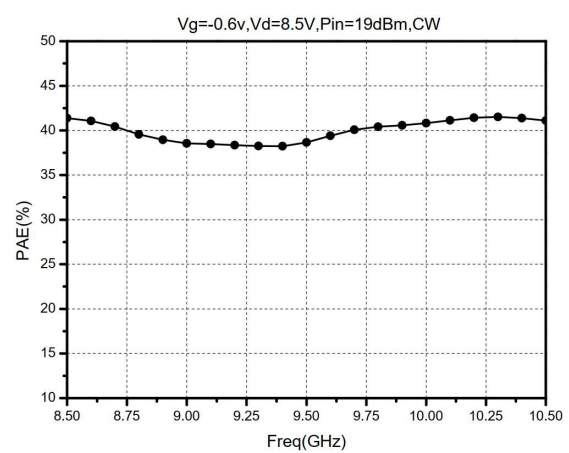
Symbol	Parameter	Min	Typical	Max	Unit
Psat	Saturated Output Power	41	41.5	-	dBm
PAE	Power Added Efficiency	38	40	-	%
Gp	Saturated Power Gain	-	23	-	dB
ΔGp	Power Gain Flatness	-	± 0.5	-	dB
Glin	Linear Gain	-	26	-	dB
VSWRin	Input Voltage standing-wave ratio	-	1.8	-	-

Test Curves

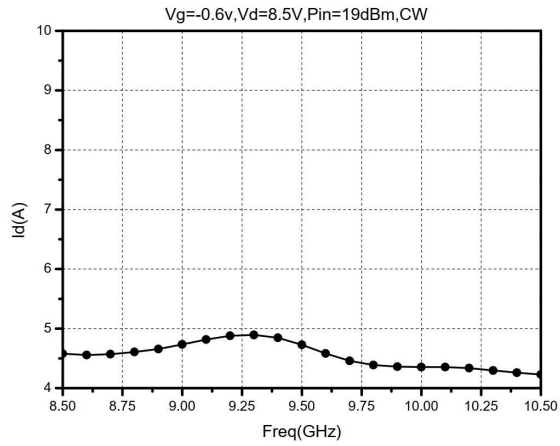
Output Power vs. Freq



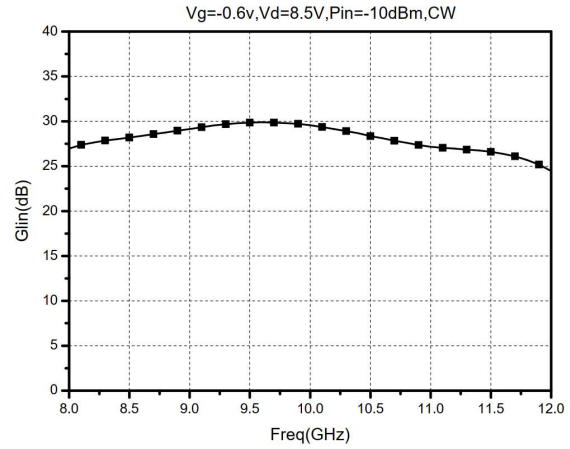
PAE vs. Freq



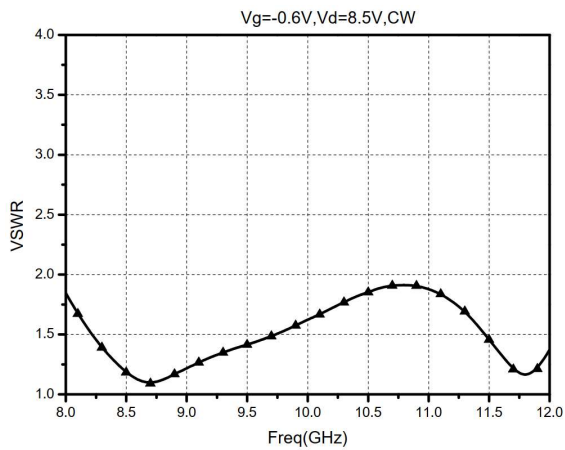
Drain Current vs. Freq



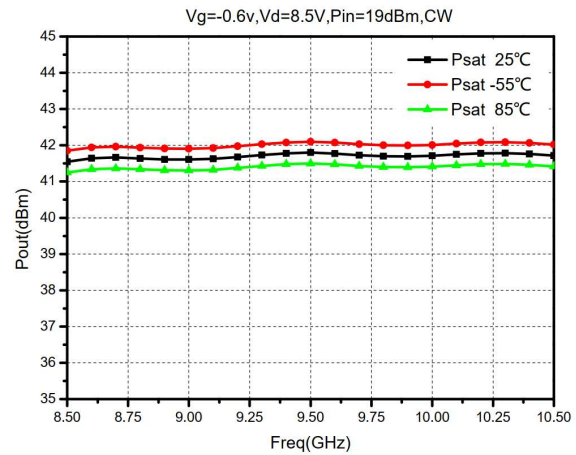
Linear Gain vs. Freq



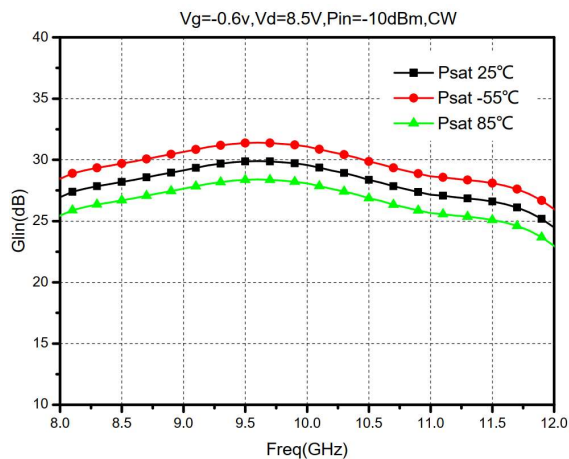
VSWR vs. Freq



Output Power vs. Freq vs. Temperature



Linear Gain vs. Freq vs. Temperature



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	9V	
I _d	Drain Current	6A	
V _g	Gate Voltage	-2V	
I _g	Gate Current	100mA	
P _d	DC Power Consumption	45W	
P _{in}	Input Power	28dBm	
T _{ch}	Channel Temperature	150°C	
T _m	Mounting Temperature	300°C	30s, N ₂ Protection
T _{stg}	Storage Temperature	-55~150°C	

Exceeding any one or combination of these limits may cause permanent damage.

